

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage			V _{GSS}	±10	V
Continuous Drain Current (Note 5) V_{GS} = -4.5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$ $T_C = +25^{\circ}C$	۱ _D	-18.0 -14.5 -40	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-80	A
Maximum Continuous Body Diode Forward Current (Note 5)			Is	-2.2	A
Avalanche Current (Note 7) L=0.1mH			I _{AS}	-23	A
Avalanche Energy (Note 7) L=0.1mH			E _{AS}	28	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Dowar Dissinction (Note E)	T _A = +25°C	Р	2.3	W
Total Power Dissipation (Note 5)	T _C = +25°C	PD	41	
Thermal Resistance, Junction to Ambient	(Note 5)	Р	56	°C/W
	(Note 6)	$R_{\theta JA}$	124	
Thermal Resistance, Junction to Case	R _{0JC}	6.8		
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_D = -250 \mu A$
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	$V_{DS} = -16V, V_{GS} = 0V$
Gate-Source Leakage	IGSS	—	_	±100	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-0.4		-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
		—	4.2	6.7	mΩ	V _{GS} = -4.5V, I _D = -15A
Static Drain-Source On-Resistance	R _{DS(ON)}	_	5.4	9.0		$V_{GS} = -2.5V, I_D = -10A$
		_	7	_		$V_{GS} = -1.8V, I_D = -1A$
Diode Forward Voltage	V _{SD}	_	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -10A$
DYNAMIC CHARACTERISTICS (Note 9)			•	•		
Input Capacitance	Ciss	—	5940	_		V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	Coss	—	835	_	pF	
Reverse Transfer Capacitance	Crss	_	728	_		
Gate Resistance	R _G	—	3.0	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge (V _{GS} = -4.5V)	Qg	—	75	_		
Total Gate Charge (V _{GS} = -10V)	Qg	—	156	_	nC	$V_{DD} = -10V, I_D = -20A$
Gate-Source Charge	Q _{gs}	—	8.8	_	nc	
Gate-Drain Charge	Q _{gd}	—	22	_		
Turn-On Delay Time	t _{D(ON)}	_	10.7	_		$V_{GS} = -4.5V, V_{DD} = -10V,$ $R_G = 1\Omega, I_D = -10A$
Turn-On Rise Time	t _R	_	23	_		
Turn-Off Delay Time	t _{D(OFF)}	_	121	_	ns	
Turn-Off Fall Time	t _F	_	109			
Reverse Recovery Time	t _{RR}		60		ns	I _F = -10A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{RR}	_	47	_	nC	I _F = -10A, di/dt = 100A/µs

Notes: 5. R_{0JA} is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. R_{0JC} is guaranteed by design while R_{0JA} is determined by the user's board design.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

7 .UIS in production with L =0.1mH, $T_{\rm J}$ = +25°C

8. Short duration pulse test used to minimize self-heating effect.

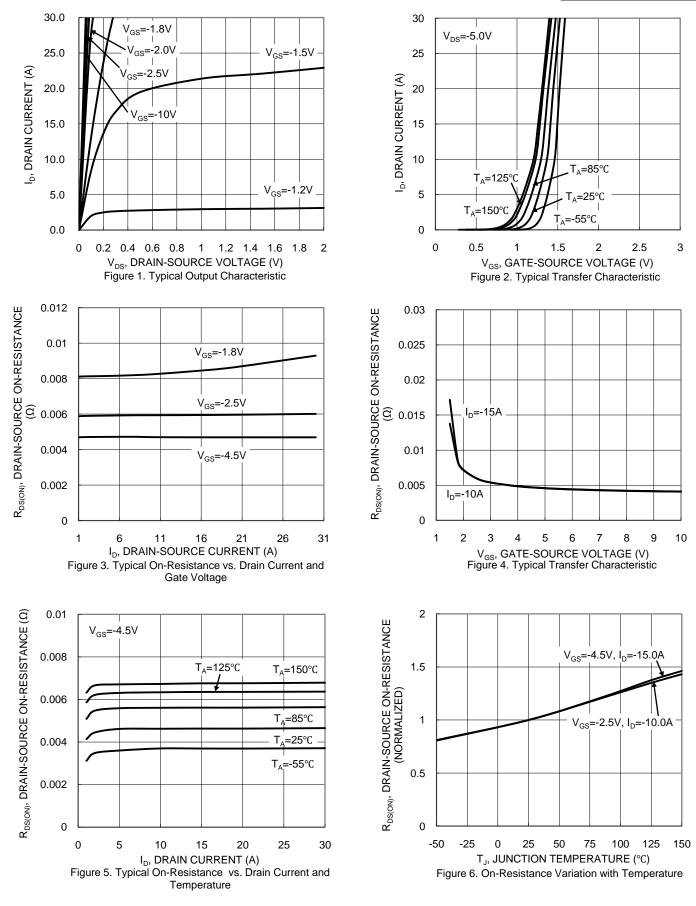
9. Guaranteed by design. Not subject to product testing.

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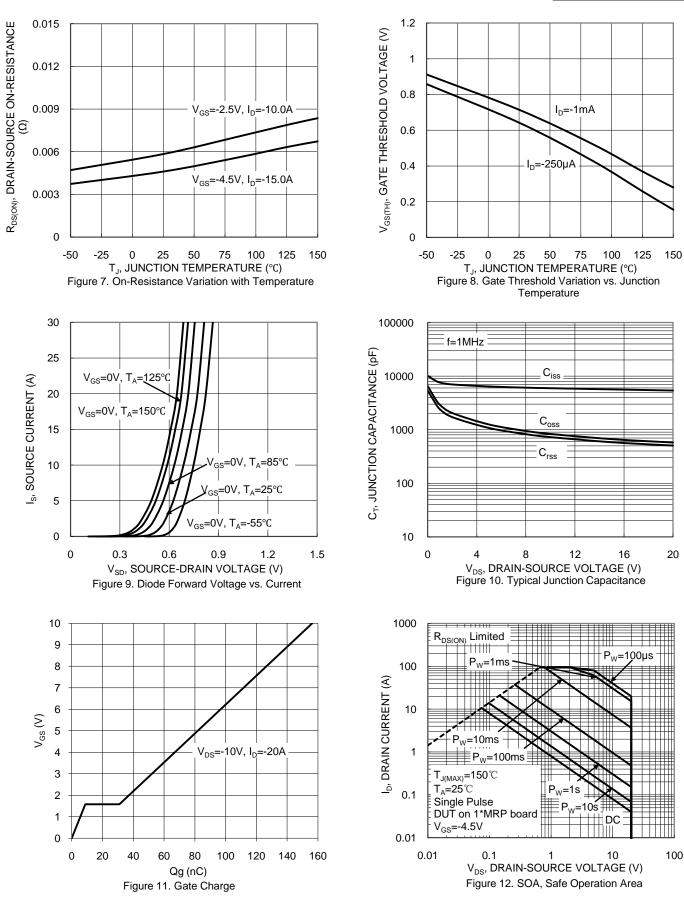


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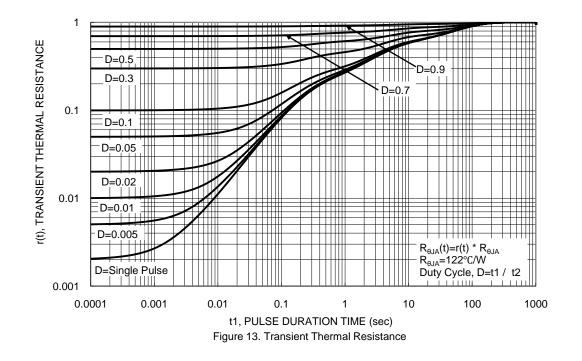
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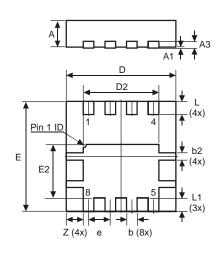
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Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



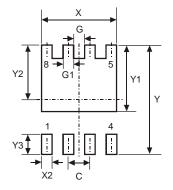
POWERDI3333-8					
Dim	Min	Max	Тур		
D	3.25	3.35	3.30		
Е	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
E2	1.56	1.66	1.61		
Α	0.75	0.85	0.80		
A1	0	0.05	0.02		
A3	-	-	0.203		
b	0.27	0.37	0.32		
b2	-	-	0.20		
L	0.35	0.45	0.40		
L1	_	-	0.39		
е	I	_	0.65		
Z	_	_	0.515		
All Dimensions in mm					

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Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.650
G	0.230
G1	0.420
Y	3.700
Y1	2.250
Y2	1.850
Y3	0.700
Х	2.370
X2	0.420

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